



InGaN-based UV photodiode

Model: GT-UVV-L

General Features:

- Indium Gallium Nitride Based Material
- Photovoltaic mode operation
- TO-46 metal housing
- High responsivity and low dark current

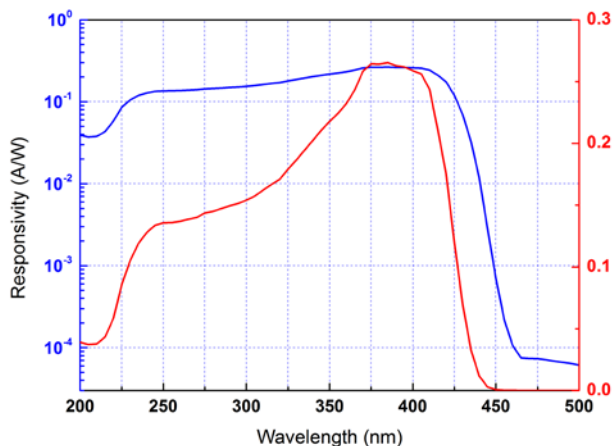


Applications: UV LED Monitoring, UV radiation dose measurement, UV Curing

Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T_{opt}	-25-85	°C
Storage temperature range	T_{sto}	-40-85	°C
Soldering temperature (3 s)	T_{sol}	260	°C
Reverse voltage	V_{r-max}	-10	V
General characteristics (25 °C)			
Chip size	A	1	mm ²
Dark current ($V_r = -5$ V)	I_d	<1	nA
Temperature coefficient	T_c	0.05	%/°C
Capacitance (at 0 V and 1 MHz)	C_p	60	pF
Spectral response characteristics (25 °C)			
Wavelength of peak responsivity	λ_p	385	nm
Peak responsivity (at 385 nm)	R_{max}	0.267	A/W
Spectral response range ($R=0.1 \times R_{max}$)	-	200-440	nm
UV-visible rejection ratio ($R_{max}/R_{400\text{ nm}}$)	-	$>10^4$	-

Spectral response



Package dimensions

